











SN74LVC1G08

ZHCSJR2Z - APRIL 1999 - REVISED MAY 2019

SN74LVC1G08 单路双输入正与门

1 特性

- 采用具有 0.5mm 间距的超小型 0.64mm² 封装 (DPW)
- 支持 5V V_{CC} 运行
- 输入电压高达 5.5V
- 支持向下转换到 Vcc
- 电压为 3.3V 时, t_{pd} 最大值为 3.6ns
- 低功耗, I_{CC} 最大值为 10μA
- 电压为 3.3V 时,输出驱动为 ±24mA
- Ioff 支持带电插入、局部关断模式和后驱动保护
- 闩锁性能超过 100mA, 符合 JESD 78 II 类规范
- ESD 保护性能超过 JESD 22 规范要求
 - 2000V 人体放电模型 (A114-A)
 - 200V 机器模型 (A115-A)
 - 1000V 充电器件模型 (C101)

2 应用

- ATCA 解决方案
- 主动噪声消除 (ANC)
- 条形码扫描仪
- 血压监护仪
- CPAP 呼吸机
- 电缆解决方案
- DLP 3D 机器视觉、高光谱成像、光纤网络和光谱 分析
- 电子书
- 嵌入式 PC
- 现场变送器:温度或湿度传感器
- 指纹识别
- 制热、通风与空调控制 (HVAC)
- 网络附属存储 (NAS)
- 服务器主板和电源装置 (PSU)
- 软件定义无线电 (SDR)
- 电视: 高清电视 (HDTV)、LCD 电视和数字电视
- 视频通信系统
- 无线数据存取卡、耳机、键盘、鼠标和 LAN 卡
- X 射线: 行李扫描仪、医疗和牙科

3 说明

按照设计,此单路双输入正与门可在 1.65V 至 5.5V Vcc 电压下运行。

SN74LVC1G08 器件以正逻辑执行布尔函数或 $Y = A \cdot B \text{ or } Y = \overline{A + B}$ 。

CMOS 器件具有高输出驱动,同时在宽 V_{CC} 工作范围内保持低静态功率耗散。

SN74LVC1G08 采用多种封装,包括外形尺寸为 0.8mm × 0.8mm 的超小型 DPW 封装。

器件信息⁽¹⁾

器件名称	封装	封装尺寸
	SOT-23 (5)	2.9mm × 1.6mm
	SC70 (5)	2.0mm x 1.25mm
SN74LVC1G08	X2SON (4)	0.8mm × 0.8mm
	SON (6)	1.45mm × 1.0mm
	SON (6)	1.0mm × 1.0mm

(1) 如需了解所有可用封装,请参阅产品说明书末尾的可订购产品 附录。





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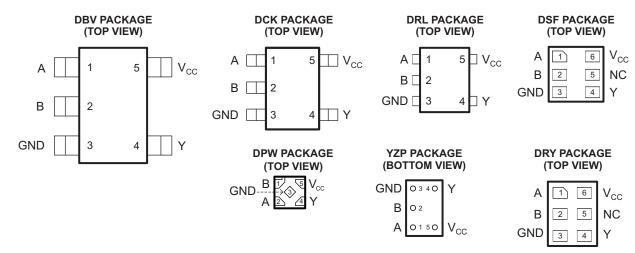
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4 修订历史记录

Cł	hanges from Revision Y (April 2014) to Revision Z	Page
•	Added T _J (max) spec to Absolute Maximum Ratings table	4
•	Moved T _{stq} spec from Handling Ratings table to Absolute Maximum Ratings table	4
<u>•</u>	Renamed Handling Ratings table to ESD Ratings table	4
Cl	hanges from Revision X (March 2014) to Revision Y	Page
•	Updated Handling Ratings table.	4
•	Added Thermal Information table.	5
•	Added Typical Characteristics.	7
•	Added Detailed Description section.	10
•	Added Application and Implementation section.	11
•	Added Power Supply Recommendations section.	12
<u>•</u>	Added Layout section.	12
Cł	hanges from Revision W (July 2013) to Revision X	Page
•	已添加 应用	1
•	已添加 添加了器件信息表	1
<u>•</u>	Moved T _{stg} to Handling Ratings table.	
Cł	hanges from Revision V (November 2012) to Revision W	Page
•	Added parameter values for –40 to 125°C temperature ratings	6



5 Pin Configuration and Functions



NC – No internal connection
See mechanical drawings for dimensions.

Pin Functions

	Pl	IN		
NAME	DBV, DCK, DRL, YZP	DRY, DSF	DPW	DESCRIPTION
Α	1	1	2	Input
В	2	2	1	Input
GND	3	3	3	Ground
Υ	4	4	4	Output
V _{cc}	5	6	5	Power pin
NC		5		Not connected



6 Specifications

6.1 Absolute Maximum Ratings⁽¹⁾

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V _{CC}	Supply voltage range		-0.5	6.5	V
VI	Input voltage range ⁽²⁾		-0.5	6.5	V
Vo	Voltage range applied to any output in the high-i	mpedance or power-off state ⁽²⁾	-0.5	6.5	V
Vo	Voltage range applied to any output in the high of	or low state (2)(3)	-0.5	V _{CC} + 0.5	V
I _{IK}	Input clamp current	V _I < 0		-50	mA
I _{OK}	Output clamp current	V _O < 0		-50	mA
Io	Continuous output current			±50	mA
	Continuous current through V _{CC} or GND			±100	mA
T _J (max)	Junction temperature	nuous current through V _{CC} or GND		150	°C
T _{stg}	Storage temperature		-65	150	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

			MIN	MAX	UNIT
V	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins (1)	0	2000	V
V _(ESD)	Electrostatic discharge	Charged device model (CDM), per JEDEC specification JESD22-C101, all pins (2)	0	1000	V

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

⁽²⁾ The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.

⁽³⁾ The value of V_{CC} is provided in the *Recommended Operating Conditions* table.

⁽²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



6.3 Recommended Operating Conditions⁽¹⁾

			MIN	MAX	UNIT		
V	Cumply yeltogo	Operating	1.65	5.5	V		
V _{CC}	Supply voltage	Data retention only	1.5		V		
		V _{CC} = 1.65 V to 1.95 V	0.65 × V _{CC}				
	High level input voltage	V _{CC} = 2.3 V to 2.7 V	1.7		V		
V _{IH}	High-level input voltage	V _{CC} = 3 V to 3.6 V	2		V		
		V _{CC} = 4.5 V to 5.5 V	0.7 × V _{CC}				
		V _{CC} = 1.65 V to 1.95 V		0.35 × V _{CC}			
.,	Lave lavel in put valtage	V _{CC} = 2.3 V to 2.7 V		0.7			
V _{IL}	Low-level input voltage	V _{CC} = 3 V to 3.6 V		0.8	V		
		V _{CC} = 4.5 V to 5.5 V		0.3 × V _{CC}			
VI	Input voltage		0	5.5	V		
Vo	Output voltage		0	V_{CC}	V		
		V _{CC} = 1.65 V		-4			
		V _{CC} = 2.3 V		-8			
I _{OH}	High-level output current	V 2V		-16	mA		
		V _{CC} = 3 V		-24			
		V _{CC} = 4.5 V		-32			
		V _{CC} = 1.65 V		4			
		V _{CC} = 2.3 V		8			
I _{OL}	Low-level output current	V 0 V		16	mA		
		V _{CC} = 3 V		24			
		V _{CC} = 4.5 V		32			
		$V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}, 2.5 \text{ V} \pm 0.2 \text{ V}$		20			
Δt/Δν	Input transition rise or fall rate	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$		10			
		$V_{CC} = 5 \text{ V} \pm 0.5 \text{ V}$		5			
T _A	Operating free-air temperature		-40	125	°C		

⁽¹⁾ All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

6.4 Thermal Information

•	morniar innormation							
				SN74L	VC1G08			
	THERMAL METRIC ⁽¹⁾	DBV	DCK	DRL	DRY	YZP	DPW	UNIT
		5 PINS	5 PINS	5 PINS	6 PINS	5 PINS	4 PINS	1
$R_{\theta JA}$	Junction-to-ambient thermal resistance	207.6	283.1	242.9	438.8	130	340	°C/W
$R_{\theta JCtop}$	Junction-to-case (top) thermal resistance	145.2	92.3	77.5	276.8	54	215	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	53.5	60.9	77.5	271.7	51	294	°C/W
ΨЈТ	Junction-to-top characterization parameter	37.5	1.7	9.6	83.8	1	41	°C/W
ΨЈВ	Junction-to-board characterization parameter	53.1	60.1	77.3	271.4	50	294	°C/W
$R_{\theta JCbot}$	Junction-to-case (bottom) thermal resistance	-	_	_	_	_	250	°C/W

⁽¹⁾ For more information about traditional and new thermal metrics, see the Semiconductor and IC package thermal metrics application report



6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

P.A	ARAMETER	TEST CONDITIONS	V _{CC}	-40°0	C to 85°C		to 125°C MENDED	UNIT	
				MIN	TYP ⁽¹⁾ MAX	MIN	TYP MAX		
		$I_{OH} = -100 \mu A$	1.65 V to 5.5 V	V _{CC} - 0.1		V _{CC} - 0.15			
		$I_{OH} = -4 \text{ mA}$	1.65 V	1.2	1.2				
.,		$I_{OH} = -8 \text{ mA}$	2.3 V	1.9		1.9		V	
V _{OH}	$I_{OH} = -16 \text{ mA}$ $I_{OH} = -24 \text{ mA}$		3 V	2.4		2.4		V	
			3 V	2.3		2.3			
		$I_{OH} = -32 \text{ mA}$	4.5 V	3.8		3.8			
	I_{OL} = 100 μ A		1.65 V to 5.5 V		0.1		0.1		
		I _{OL} = 4 mA	1.65 V		0.45		0.45		
		I _{OL} = 8 mA	2.3 V		0.3			3 V	
V _{OL}		I _{OL} = 16 mA	3 V		0.4		0.4	v	
		I _{OL} = 24 mA	3 V	0.55		0.55			
		I _{OL} = 32 mA	4.5 V		0.55		0.55		
I	A or B inputs	V _I = 5.5 V or GND	0 to 5.5 V		±5		±5	μА	
I _{off}		V _I or V _O = 5.5 V	0		±10		±10	μΑ	
I _{CC}		$V_I = 5.5 \text{ V or GND}, \qquad I_O = 0$	1.65 V to 5.5 V		10		10	μΑ	
ΔI_{CC}		One input at V _{CC} – 0.6 V, Other inputs at V _{C C} or GND	3 V to 5.5 V		500		500	μΑ	
Ci		V _I = V _{CC} or GND	3.3 V		4		4	pF	

⁽¹⁾ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

6.6 Switching Characteristics, $C_L = 15 pF$

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 3)

						–40°C t	o 85°C				
PARAMETER	PARAMETER FROM (INPUT)	TO (OUTPUT)	V _{CC} = 1.8 V ± 0.15 V		V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 5 V ± 0.5 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd}	A or B	Υ	1.5	7.2	0.7	4.4	0.8	3.6	0.8	3.4	ns

6.7 Switching Characteristics, 1.8 V and 2.5 V⁽¹⁾

over recommended operating free-air temperature range, (unless otherwise noted) (see Figure 4)

			то	-40°C to 85°C		-40°C to	125°C	-40°C to 85°C		–40°C to		
		FROM				RECOMMENDED		-40 C to 65 C		RECOMMENDED		
	PARAMETER	(INPUT)		(OUTPUT)	V _{CC} = 1.8 V ± 0.15 V		V _{CC} = 2 ± 0.2		V _{CC} = 2 ± 0.2	UNIT		
				MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
	t _{pd}	A or B	Y	2.4	8	2.4	10	1.1	5.5	1.1	7	ns

⁽¹⁾ On products compliant to MIL-PRF-38535, this parameter is not production tested.



6.8 Switching Characteristics, 3.3 V and 5 $V^{(1)}$

over recommended operating free-air temperature range, $C_L = 30 \text{ pF}$ or 50 pF (unless otherwise noted) (see Figure 4)

			40°C to	0E°C	-40°C to	125°C	−40°C to	0E°C	–40°C to	125°C	
PARAMETER	FROM (INPUT)	TO (OUTPUT)	–40°C to 85°C		RECOMMENDED		-40 C 10 03 C		RECOMMENDED		
			V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 5 V ± 0.5 V		V _{CC} = 5 V ± 0.5 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd}	A or B	Υ	1	4.5	1	6	1	4	1	5	ns

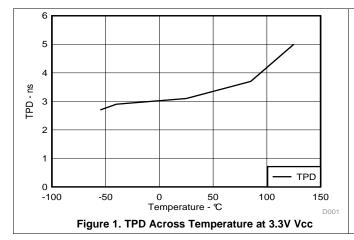
⁽¹⁾ On products compliant to MIL-PRF-38535, this parameter is not production tested.

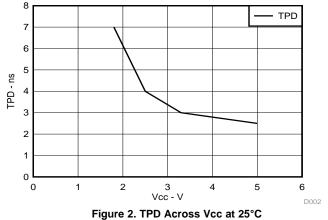
6.9 Operating Characteristics

 $T_A = 25^{\circ}C$

	PARAMETER	TEST	V _{CC} = 1.8 V	$V_{CC} = 2.5 V$	$V_{CC} = 3.3 \text{ V}$	V _{CC} = 5 V	UNIT
	FARAMETER	CONDITIONS	TYP	TYP	TYP	TYP	UNIT
$C_{\mathfrak{p}}$	Power dissipation capacitance	f = 10 MHz	21	24	26	31	pF

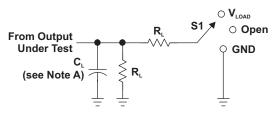
6.10 Typical Characteristics







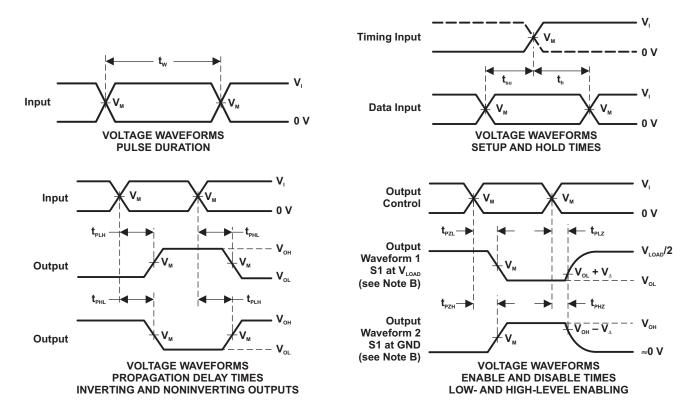
7 Parameter Measurement Information



TEST	S1
t _{PLH} /t _{PHL}	Open
t _{PLZ} /t _{PZL}	V _{LOAD}
t _{PHZ} /t _{PZH}	GND

	\sim	A	D	\sim		_		-
_	U	н	D	u	ĸ	u	U	ш

.,	INI	PUTS		v		-	
V _{cc}	V,	t,/t,	V _M	V _{LOAD}	C _L	R _∟	V _Δ
1.8 V ± 0.15 V	V _{cc}	≤2 ns	V _{cc} /2	2 × V _{cc}	15 pF	1 M Ω	0.15 V
$2.5~\textrm{V}~\pm~0.2~\textrm{V}$	V _{cc}	≤2 ns	V _{cc} /2	2 × V _{cc}	15 pF	1 M Ω	0.15 V
$3.3~V~\pm~0.3~V$	3 V	≤2.5 ns	1.5 V	6 V	15 pF	1 M Ω	0.3 V
5 V ± 0.5 V	V _{cc}	≤2.5 ns	V _{cc} /2	2 × V _{cc}	15 pF	1 M Ω	0.3 V



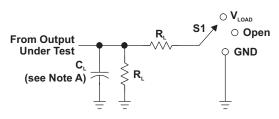
NOTES: A. C, includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_{\circ} = 50 Ω .
- D. The outputs are measured one at a time, with one transition per measurement.
- E. t_{PLZ} and \dot{t}_{PHZ} are the same as t_{dis} .
- F. $t_{\mbox{\tiny PZL}}$ and $t_{\mbox{\tiny PZH}}$ are the same as $t_{\mbox{\tiny en}}.$
- G. t_{PlH} and t_{PHl} are the same as t_{pd} .
- H. All parameters and waveforms are not applicable to all devices.

Figure 3. Load Circuit and Voltage Waveforms



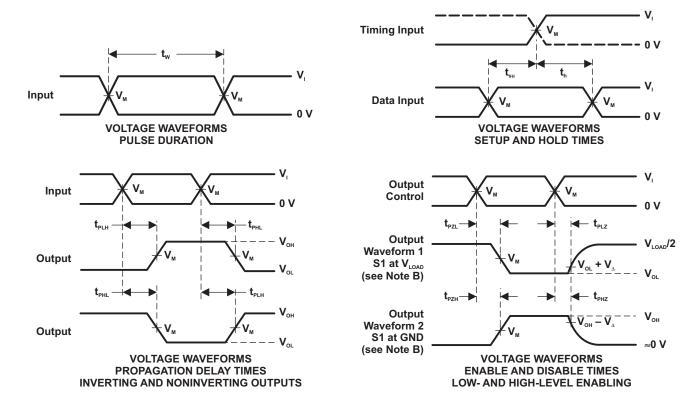
Parameter Measurement Information (continued)



TEST	S1
t _{PLH} /t _{PHL}	Open
t _{PLZ} /t _{PZL}	V _{LOAD}
t _{PHZ} /t _{PZH}	GND

LOAD CIRCUIT

.,	INI	INPUTS		.,		1	.,
V _{cc}	V,	t,/t,	V _M	V _{LOAD}	C _L	$R_{\scriptscriptstyle L}$	V _A
1.8 V ± 0.15 V	V _{cc}	≤2 ns	V _{cc} /2	2 × V _{cc}	30 pF	1 k Ω	0.15 V
2.5 V ± 0.2 V	V _{cc}	≤2 ns	V _{cc} /2	2 × V _{cc}	30 pF	500 Ω	0.15 V
$3.3~V~\pm~0.3~V$	3 V	≤2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V
5 V ± 0.5 V	V _{cc}	≤2.5 ns	V _{cc} /2	2 × V _{cc}	50 pF	500 Ω	0.3 V



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_0 = 50 \,\Omega$.
- D. The outputs are measured one at a time, with one transition per measurement.
- E. t_{PLZ} and \dot{t}_{PHZ} are the same as t_{dis} .
- F. t_{PZL} and t_{PZH} are the same as t_{en} .
- G. t_{PLH}^{rzt} and t_{PHL}^{rzn} are the same as t_{pd}^{rd} .
- H. All parameters and waveforms are not applicable to all devices.

Figure 4. Load Circuit and Voltage Waveforms



8 Detailed Description

8.1 Overview

The SN74LVC1G08 device contains one 2-input positive AND gate device and performs the Boolean function $Y = A \cdot B \text{ or } Y = \overline{A + B}$. This device is fully specified for partial-power-down applications using loff. The loff circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

The DPW package technology is a major breakthrough in IC packaging. Its tiny 0.64 mm square footprint saves significant board space over other package options while still retaining the traditional manufacturing friendly lead pitch of 0.5 mm.

8.2 Functional Block Diagram



8.3 Feature Description

- · Wide operating voltage range.
 - Operates from 1.65 V to 5.5 V.
- Allows down voltage translation.
- Inputs accept voltages to 5.5 V.
- I_{off} feature allows voltages on the inputs and outputs when V_{CC} is 0 V.

8.4 Device Functional Modes

Table 1. Function Table

INP	UTS	OUTPUT
Α	В	Υ
Н	Н	Н
L	X	L
X	L	L

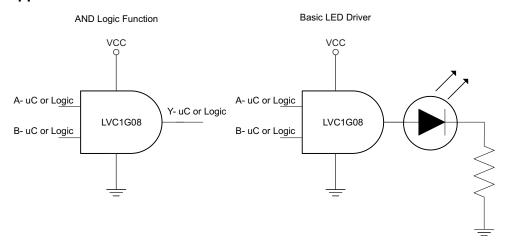


9 Application and Implementation

9.1 Application Information

The SN74LVC1G08 is a high drive CMOS device that can be used for implementing AND logic with a high output drive, such as an LED application. It can produce 24 mA of drive current at 3.3 V making it Ideal for driving multiple outputs and good for high speed applications up to 100 MHz. The inputs are 5.5 V tolerant allowing it to translate down to $V_{\rm CC}$.

9.2 Typical Application



9.2.1 Design Requirements

This device uses CMOS technology and has balanced output drive. Care should be taken to avoid bus contention because it can drive currents that would exceed maximum limits. The high drive will also create fast edges into light loads so routing and load conditions should be considered to prevent ringing.

9.2.2 Detailed Design Procedure

- 1. Recommended Input Conditions
 - Rise time and fall time specs. See (Δt/ΔV) in the Recommended Operating Conditions table.
 - Specified high and low levels. See (V_{IH} and V_{IL}) in the Recommended Operating Conditions table.
 - Inputs are overvoltage tolerant allowing them to go as high as (V_I max) in the Recommended Operating
 Conditions table at any valid V_{CC}.

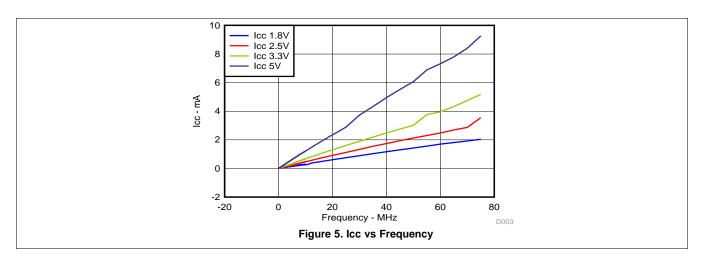
2. Recommend Output Conditions

- Load currents should not exceed (I_O max) per output and should not exceed total current (continuous current through V_{CC} or GND) for the part. These limits are located in the Absolute Maximum Ratings table.
- Outputs should not be pulled above V_{CC}.



Typical Application (continued)

9.2.3 Application Curves



10 Power Supply Recommendations

The power supply can be any voltage between the min and max supply voltage rating located in the *Recommended Operating Conditions* table.

Each Vcc pin should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, a 0.1- μ F capacitor is recommended and if there are multiple Vcc pins then 0.01- μ F or 0.022- μ F capacitor is recommended for each power pin. It is ok to parallel multiple bypass capacitors to reject different frequencies of noise. 0.1- μ F and 1- μ F capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power pin as possible for best results.

11 Layout

11.1 Layout Guidelines

When using multiple bit logic devices inputs should not ever float. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such input pins should not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. Specified below are the rules that must be observed under all circumstances. All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that should be applied to any particular unused input depends on the function of the device. Generally they will be tied to Gnd or Vcc whichever make more sense or is more convenient.

11.2 Layout Example





12 器件和文档支持

12.1 商标

All trademarks are the property of their respective owners.

12.2 静电放电警告



这些装置包含有限的内置 ESD 保护。 存储或装卸时,应将导线一起截短或将装置放置于导电泡棉中,以防止 MOS 门极遭受静电损伤。

12.3 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

13 机械、封装和可订购信息

以下页面包含机械、封装和可订购信息。这些信息是指定器件的最新可用数据。数据如有变更,恕不另行通知,且不会对此文档进行修订。如需获取此数据表的浏览器版本,请查阅左侧的导航栏。





10-Dec-2020

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material (6)	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
SN74LVC1G08DBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(C085, C08F, C08J, C08K, C08R, C 08T) (C08P, C08S)	Samples
SN74LVC1G08DBVRE4	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C08 C08P	Samples
SN74LVC1G08DBVRG4	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM		C08 C08P	Samples
SN74LVC1G08DBVT	ACTIVE	SOT-23	DBV	5	250	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(C085, C08F, C08J, C08K, C08R) (C08H, C08P, C08S)	Samples
SN74LVC1G08DBVTE4	ACTIVE	SOT-23	DBV	5	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C08 C08P	Samples
SN74LVC1G08DCK3	ACTIVE	SC70	DCK	5	3000	RoHS & Non-Green	SNBI	Level-1-260C-UNLIM	-40 to 125	(CEF, CEZ)	Samples
SN74LVC1G08DCKR	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(CE5, CEF, CEJ, CE K, CER, CET) (CEH, CEP, CES)	Samples
SN74LVC1G08DCKRE4	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	CE5 CES	Samples
SN74LVC1G08DCKRG4	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	CE5 CES	Samples
SN74LVC1G08DCKT	ACTIVE	SC70	DCK	5	250	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(CE5, CEF, CEJ, CE K, CER, CET) (CEH, CEP, CES)	Samples
SN74LVC1G08DCKTE4	ACTIVE	SC70	DCK	5	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	CE5 CES	Samples
SN74LVC1G08DCKTG4	ACTIVE	SC70	DCK	5	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	CE5 CES	Samples
SN74LVC1G08DPWR	ACTIVE	X2SON	DPW	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	M4	Samples
SN74LVC1G08DRLR	ACTIVE	SOT-5X3	DRL	5	4000	RoHS & Green	NIPDAU NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	(CE7, CER)	Samples



PACKAGE OPTION ADDENDUM

10-Dec-2020

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
SN74LVC1G08DRLRG4	ACTIVE	SOT-5X3	DRL	5	4000	RoHS & Green	NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	(CE7, CER)	Samples
SN74LVC1G08DRY2	ACTIVE	SON	DRY	6	5000	RoHS & Green	NIPDAU NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	CE	Samples
SN74LVC1G08DRYR	ACTIVE	SON	DRY	6	5000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	CE	Samples
SN74LVC1G08DSF2	ACTIVE	SON	DSF	6	5000	RoHS & Green	NIPDAU NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	CE	Samples
SN74LVC1G08DSFR	ACTIVE	SON	DSF	6	5000	RoHS & Green	NIPDAU NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	CE	Samples
SN74LVC1G08YZPR	ACTIVE	DSBGA	YZP	5	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	(CE, CE7)	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.



PACKAGE OPTION ADDENDUM

10-Dec-2020

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TAPE AND REEL INFORMATION



TAPE DIMENSIONS + K0 - P1 - B0 W Cavity - A0 -

	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



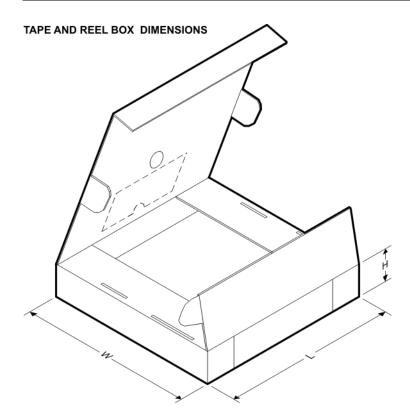
*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LVC1G08DBVR	SOT-23	DBV	5	3000	178.0	9.2	3.3	3.23	1.55	4.0	8.0	Q3
SN74LVC1G08DBVR	SOT-23	DBV	5	3000	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
SN74LVC1G08DBVRG4	SOT-23	DBV	5	3000	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
SN74LVC1G08DBVT	SOT-23	DBV	5	250	178.0	9.2	3.3	3.23	1.55	4.0	8.0	Q3
SN74LVC1G08DBVT	SOT-23	DBV	5	250	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
SN74LVC1G08DBVT	SOT-23	DBV	5	250	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
SN74LVC1G08DCKR	SC70	DCK	5	3000	180.0	8.4	2.47	2.3	1.25	4.0	8.0	Q3
SN74LVC1G08DCKR	SC70	DCK	5	3000	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74LVC1G08DCKR	SC70	DCK	5	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
SN74LVC1G08DCKRG4	SC70	DCK	5	3000	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74LVC1G08DCKT	SC70	DCK	5	250	180.0	8.4	2.47	2.3	1.25	4.0	8.0	Q3
SN74LVC1G08DCKT	SC70	DCK	5	250	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
SN74LVC1G08DCKT	SC70	DCK	5	250	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74LVC1G08DCKTG4	SC70	DCK	5	250	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74LVC1G08DPWR	X2SON	DPW	5	3000	178.0	8.4	0.91	0.91	0.5	2.0	8.0	Q3
SN74LVC1G08DRLR	SOT-5X3	DRL	5	4000	180.0	8.4	1.98	1.78	0.69	4.0	8.0	Q3
SN74LVC1G08DRY2	SON	DRY	6	5000	180.0	8.4	1.65	1.2	0.7	4.0	8.0	Q3
SN74LVC1G08DRY2	SON	DRY	6	5000	180.0	9.5	1.6	1.15	0.75	4.0	8.0	Q3



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Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LVC1G08DRYR	SON	DRY	6	5000	180.0	9.5	1.15	1.6	0.75	4.0	8.0	Q1
SN74LVC1G08DSF2	SON	DSF	6	5000	180.0	9.5	1.16	1.16	0.5	4.0	8.0	Q3
SN74LVC1G08DSF2	SON	DSF	6	5000	180.0	8.4	1.16	1.16	0.63	4.0	8.0	Q3
SN74LVC1G08DSFR	SON	DSF	6	5000	180.0	8.4	1.16	1.16	0.5	4.0	8.0	Q2
SN74LVC1G08YZPR	DSBGA	YZP	5	3000	180.0	8.4	1.02	1.52	0.63	4.0	8.0	Q1



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LVC1G08DBVR	SOT-23	DBV	5	3000	180.0	180.0	18.0
SN74LVC1G08DBVR	SOT-23	DBV	5	3000	180.0	180.0	18.0
SN74LVC1G08DBVRG4	SOT-23	DBV	5	3000	180.0	180.0	18.0
SN74LVC1G08DBVT	SOT-23	DBV	5	250	180.0	180.0	18.0
SN74LVC1G08DBVT	SOT-23	DBV	5	250	180.0	180.0	18.0
SN74LVC1G08DBVT	SOT-23	DBV	5	250	180.0	180.0	18.0
SN74LVC1G08DCKR	SC70	DCK	5	3000	202.0	201.0	28.0
SN74LVC1G08DCKR	SC70	DCK	5	3000	180.0	180.0	18.0
SN74LVC1G08DCKR	SC70	DCK	5	3000	180.0	180.0	18.0
SN74LVC1G08DCKRG4	SC70	DCK	5	3000	180.0	180.0	18.0
SN74LVC1G08DCKT	SC70	DCK	5	250	202.0	201.0	28.0
SN74LVC1G08DCKT	SC70	DCK	5	250	180.0	180.0	18.0



PACKAGE MATERIALS INFORMATION

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Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LVC1G08DCKT	SC70	DCK	5	250	180.0	180.0	18.0
SN74LVC1G08DCKTG4	SC70	DCK	5	250	180.0	180.0	18.0
SN74LVC1G08DPWR	X2SON	DPW	5	3000	205.0	200.0	33.0
SN74LVC1G08DRLR	SOT-5X3	DRL	5	4000	202.0	201.0	28.0
SN74LVC1G08DRY2	SON	DRY	6	5000	202.0	201.0	28.0
SN74LVC1G08DRY2	SON	DRY	6	5000	184.0	184.0	19.0
SN74LVC1G08DRYR	SON	DRY	6	5000	184.0	184.0	19.0
SN74LVC1G08DSF2	SON	DSF	6	5000	184.0	184.0	19.0
SN74LVC1G08DSF2	SON	DSF	6	5000	202.0	201.0	28.0
SN74LVC1G08DSFR	SON	DSF	6	5000	210.0	185.0	35.0
SN74LVC1G08YZPR	DSBGA	YZP	5	3000	182.0	182.0	20.0

DCK (R-PDSO-G5)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
- D. Falls within JEDEC MO-203 variation AA.



DCK (R-PDSO-G5)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.





Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.









NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.





NOTES: (continued)

3. For more information, see QFN/SON PCB application report in literature No. SLUA271 (www.ti.com/lit/slua271).





NOTES: (continued)

Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.





SMALL OUTLINE TRANSISTOR



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 2. This drawing is subject to change without notice.
 3. Reference JEDEC MO-178.

- 4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

- 5. Publication IPC-7351 may have alternate designs.
- 6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)



^{7.} Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

^{8.} Board assembly site may have different recommendations for stencil design.



Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.

4211218-3/D







NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.
- 3. The size and shape of this feature may vary.





NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, refer to QFN/SON PCB application note in literature No. SLUA271 (www.ti.com/lit/slua271).





NOTES: (continued)

5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



YEA (R-XBGA-N5)

DIE-SIZE BALL GRID ARRAY



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. NanoStar \mathbf{M} package configuration.
- D. Package complies to JEDEC MO-211 variation EA.
- E. This package is tin-lead (SnPb). Refer to the 5 YZA package (drawing 4204151) for lead-free.

NanoStar is a trademark of Texas Instruments.





DIE SIZE BALL GRID ARRAY



NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.



DIE SIZE BALL GRID ARRAY



NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SNVA009 (www.ti.com/lit/snva009).



DIE SIZE BALL GRID ARRAY



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.





PLASTIC SMALL OUTLINE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
 4. Reference JEDEC registration MO-293 Variation UAAD-1



PLASTIC SMALL OUTLINE



NOTES: (continued)

- 5. Publication IPC-7351 may have alternate designs.
- 6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



PLASTIC SMALL OUTLINE



NOTES: (continued)



^{7.} Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

^{8.} Board assembly site may have different recommendations for stencil design.





NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. Reference JEDEC registration MO-287, variation X2AAF.





NOTES: (continued)

4. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).





4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



YEP (R-XBGA-N5)

DIE-SIZE BALL GRID ARRAY



NOTES: A. All linear dimensions are in millimeters.

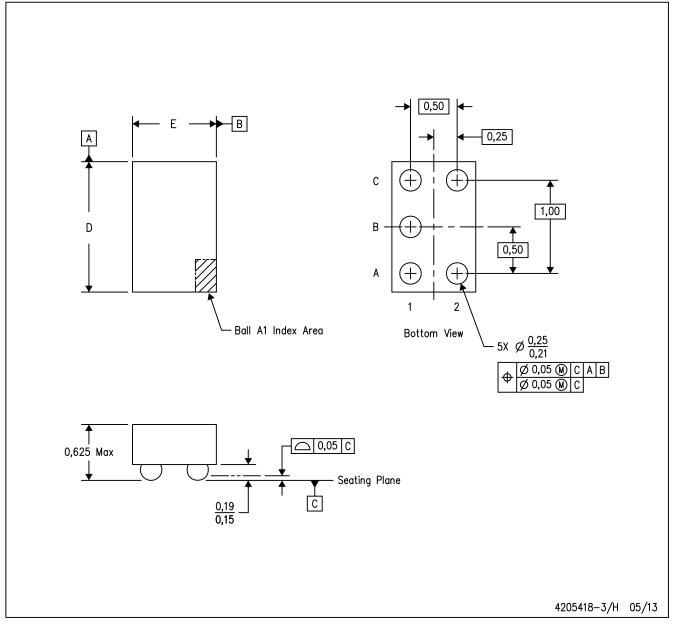
- B. This drawing is subject to change without notice.
- C. NanoStar \mathbf{M} package configuration.
- D. This package is tin-lead (SnPb). Refer to the 5 YZP package (drawing 4204741) for lead-free.

NanoStar is a trademark of Texas Instruments.



YZT (R-XBGA-N5)

DIE-SIZE BALL GRID ARRAY



NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. NanoFree™ package configuration.

NanoFree is a trademark of Texas Instruments.



YZA (R-XBGA-N5)

DIE-SIZE BALL GRID ARRAY



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. NanoFree $^{\text{TM}}$ package configuration.
- D. Package complies to JEDEC MO-211 variation EA.
- E. This package is lead-free. Refer to the 5 YEA package (drawing 4203167) for tin-lead (SnPb).

NanoFree is a trademark of Texas Instruments.



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